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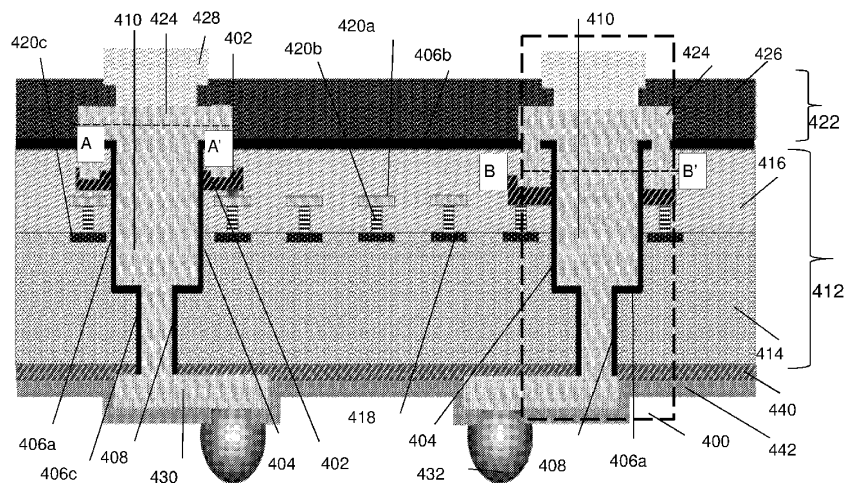
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(54) Title: ELECTRICAL CONNECTION STRUCTURE AND METHOD OF FORMING THE SAME



(57) Abstract: Various embodiments may provide a method of forming an electrical connection structure. The method may include forming a cavity on a front surface of a substrate, the substrate including an electrically conductive pad, by etching through the electrically conductive pad. The method may also include forming one or more dielectric liner layers covering an inner surface of the cavity. The method may further include forming a via hole extending from the cavity by etching through the one or more dielectric liner layers, forming one or more further dielectric liner layers covering an inner surface of the via hole. The method may additionally include depositing a suitable electrically conductive material into the cavity and the via hole to form a conductive via having a first portion in the cavity and a second portion in the via hole, a diameter of the first portion different from a diameter of the second portion.

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